

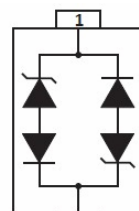


## LTBVxxC/CI

Bidirectional Ultralow Capacitance TVS ARRAY



SOD-323



BIDIRECTIONAL

### Features

- Compliance with IEC 61000-4-2 (ESD) 18 kV (Air), 10 kV (Contact)
- Compatible with IEC 61000-4-4 (EFT): 40A - 5/50ns
- 350 Watts Peak Pulse Power per Line (8 x 20 us Waveform)
- Replacement for MLV (0805)
- Protects One Power or I/O Port
- Low Clamping Voltage
- Available in Multiple Voltages Ranging From 3V to 24V
- Ultra Low Capacitance: 0.8pF (Typical)
- RoHS Compliant

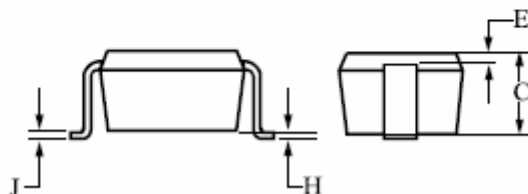
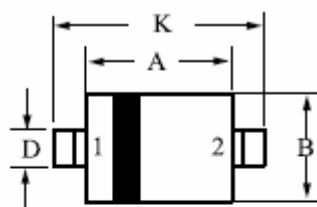
### Main applications

- Hand-Held Portable Applications
- Networking and Telecom(Ethernet 10/100/1000 Base T)
- USB Interface
- Automotive Electronics
- Serial and Parallel Ports
- Notebooks, Desktops, Servers

### Protection solution to meet

- IEC61000-4-2 Level 4, 18 kV (Air), 10 kV (Contact)

SOD-323



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.60	1.80	0.063	0.071
B	1.15	1.35	0.045	0.053
C	0.80	1.00	0.031	0.039
D	0.25	0.40	0.010	0.016
E	0.15 REF		0.006 REF	
H	0.00	0.10	0.000	0.004
J	0.089	0.177	0.0035	0.0070
K	2.30	2.70	0.091	0.106

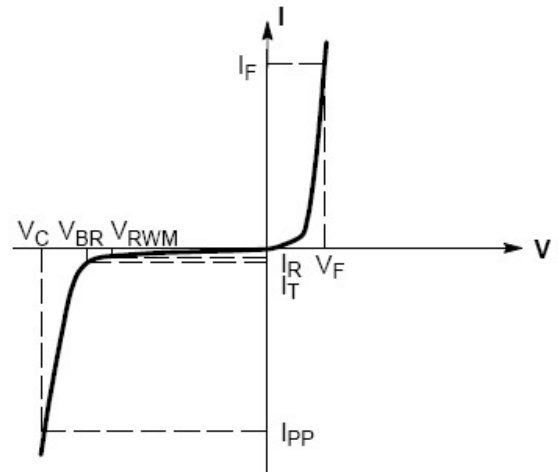
### Maximum ratings (T<sub>J</sub>=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Power Dissipation (8 X 20 μs @ TA = 25°C)	PPK	350	W
IEC61000-4-2(ESD): Contact Air	V <sub>ESD</sub>	±10 ±18	KV
ESD Voltage Per Human Body Model Per Machine Model		16 400	KV V
Operating Junction Temperature Range	T <sub>J</sub>	-40 ~ 125	°C
Storage Temperature Range	T <sub>STG</sub>	-55 ~ 150	°C
Lead Solder Temperature – Maximum (10 Second Duration)	TL	260	°C

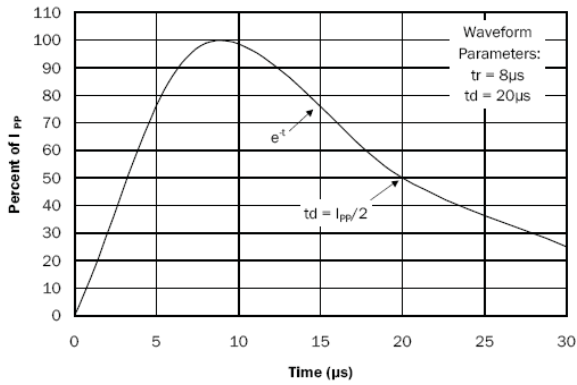
### Electrical characteristics (T<sub>J</sub> = 25°C unless otherwise noted)

Device	V <sub>RWM</sub>	V <sub>BR</sub>	V <sub>C</sub> (V)@ I <sub>PP</sub>	Max I <sub>PP</sub>	I <sub>R</sub> @ V <sub>RWM</sub>	C <sub>J</sub>	PPK
	V	V	V	A	μA	pF	W
LTBV03C	3.3	4.0	19.0	20.0	5	1.2	350
LTBV05C	5.0	6.0	18.3	17.0	5	1.2	350
LTBV08C	8.0	8.5	18.5	17.0	2	1.2	350
LTBV12C	12.0	13.3	28.6	11.0	1	1.2	350
LTBV15C	15.0	16.7	31.8	10.0	1	1.2	350
LTBV18C	18.0	20.0	45.0	8.0	1	1.2	350
LTBV24C	24.0	26.7	56.0	6.0	1	1.2	350
GBLC03CI	3.0	4.0	13.9	15.0	20	0.8	150
GBLC05CI	5.0	6.0	18.3	17.0	5	0.8	150
GBLC12CI	12.0	13.3	28.6	6.0	1	0.8	150

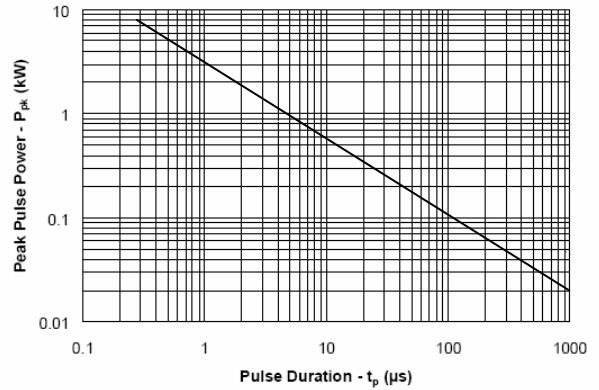
Symbol	Parameter
V <sub>RWM</sub>	Working Peak Reverse Voltage
V <sub>BR</sub>	Breakdown Voltage @ I <sub>T</sub>
V <sub>C</sub>	Clamping Voltage @ I <sub>PP</sub>
I <sub>T</sub>	Test Current
I <sub>RM</sub>	Leakage current at V <sub>RWM</sub>
I <sub>PP</sub>	Peak pulse current
C <sub>O</sub>	Off-state Capacitance
C <sub>J</sub>	Junction Capacitance



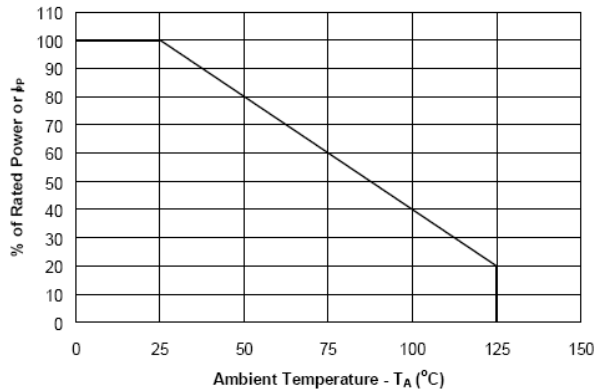
# Typical Electrical Characteristics



Pulse Waveform



Non-Repetitive Peak Pulse Power vs. Pulse Time



Power Derating Curve

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